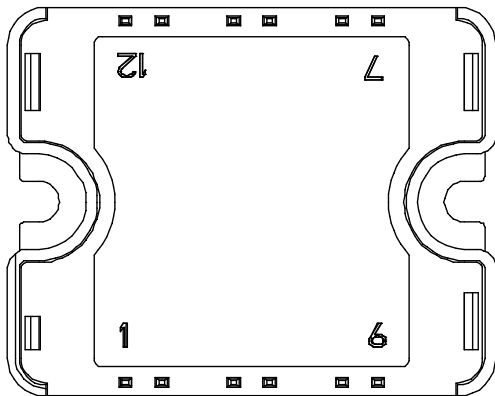
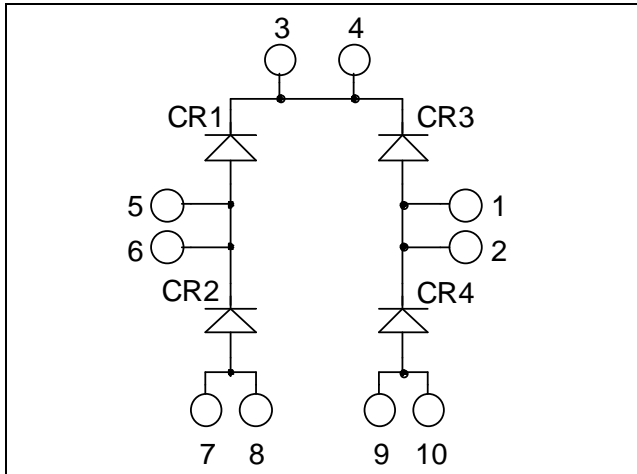


SiC Diode Full Bridge Power Module

$V_{RRM} = 1200V$
 $I_F = 10A @ T_c = 80^\circ C$



All multiple inputs and outputs must be shorted together
 3/4 ; 5/6 ; 7/8 ; 1/2 ; 9/10

Application

- Uninterruptible Power Supply (UPS)
- Induction heating
- Welding equipment
- High speed rectifiers

Features

- **SiC Schottky Diode**
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature Independent switching behavior
 - Positive temperature coefficient on VF
- Very low stray inductance
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Low losses
- Low noise switching
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_R	Maximum DC reverse Voltage	1200	V
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		
$I_{F(AV)}$	Maximum Average Forward Current	10	A
I_{FSM}	Non-Repetitive Forward Surge Current	125	
		10 μs	$T_C = 25^\circ C$

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

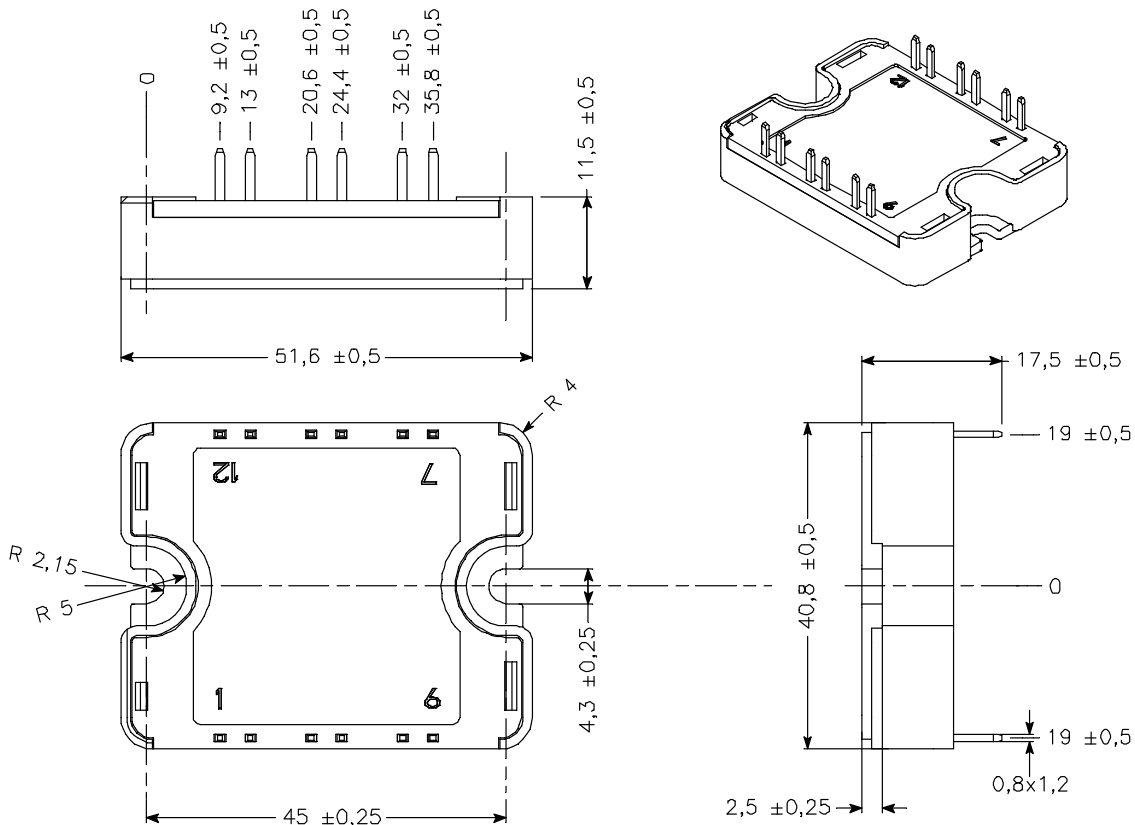
Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
V_F	Diode Forward Voltage	$I_F = 10\text{A}$	$T_j = 25^\circ\text{C}$		1.6	1.8	V
			$T_j = 175^\circ\text{C}$		2.3	3.0	
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200\text{V}$	$T_j = 25^\circ\text{C}$		32	200	μA
			$T_j = 175^\circ\text{C}$		56	1000	
Q_C	Total Capacitive Charge	$I_F = 10\text{A}, V_R = 600\text{V}$ $di/dt = 500\text{A}/\mu\text{s}$		40		nC	
C	Total Capacitance	$f = 1\text{MHz}, V_R = 200\text{V}$		96		pF	
		$f = 1\text{MHz}, V_R = 400\text{V}$		69			

Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
R_{thJC}	Junction to Case Thermal Resistance			1.8	$^\circ\text{C}/\text{W}$	
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t=1\text{ min}, I_{isol}<1\text{mA}, 50/60\text{Hz}$	2500			V	
T_J	Operating junction temperature range	-40		175	$^\circ\text{C}$	
T_{STG}	Storage Temperature Range	-40		125		
T_C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2.5	4.7	N.m
Wt	Package Weight				80	g

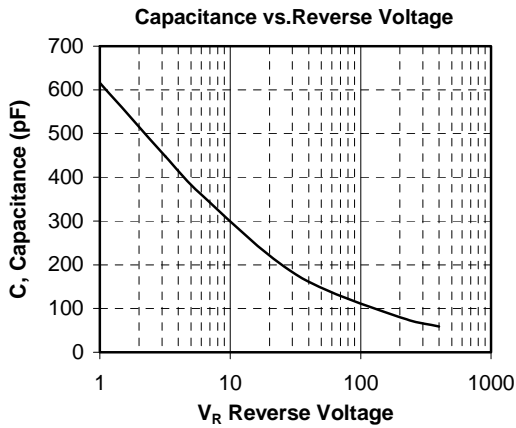
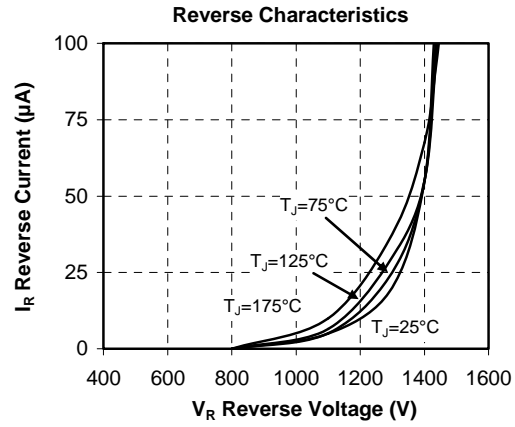
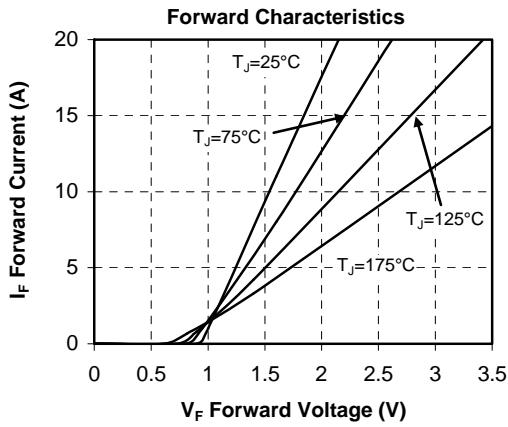
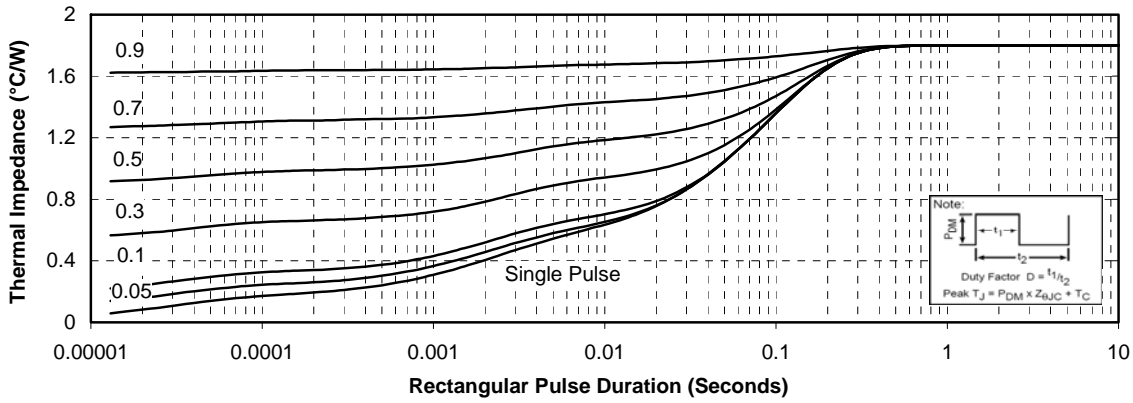
SP1 Package outline (dimensions in mm)



See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

Typical Performance Curve

Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 6,939,743 7,352,045 5,283,201 5,801,417 5,648,283 7,196,634 6,664,594 7,157,886 6,939,743 7,342,262 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.